

YG233C2,N2,D2 (8A)

(200V / 8A)

FAST RECOVERY DIODE

■ Features

- Insulated package by fully molding
- High voltage by mesa design
- High reliability

■ Applications

- High speed switching

■ Maximum ratings and characteristics

- Absolute maximum ratings

Item	Symbol	Conditions	Rating	Unit
Repetitive peak reverse voltage	V_{RRM}		200	V
Non-repetitive peak reverse voltage	V_{RSM}		200	V
Isolating voltage	V_{iso}	Terminals-to-Case, AC.1min	1500	V
Average output current	I_o	Square wave, duty=1/2, $T_c=95^\circ C$	8*	A
Surge current	I_{FSM}	Sine wave 10ms	30	A
Operating junction temperature	T_j		+150	°C
Storage temperature	T_{stg}		-40 to +150	°C

* Average forward current of centertap full wave connection

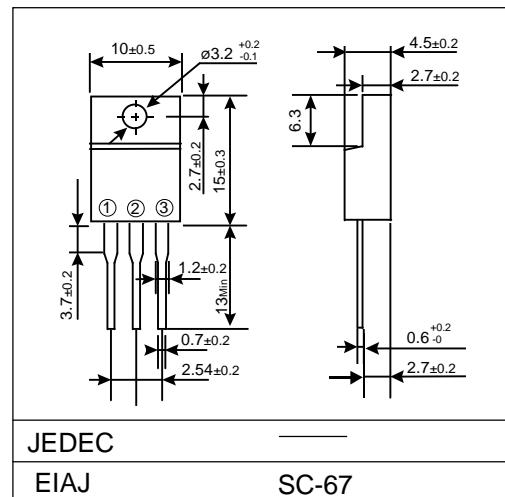
- Electrical characteristics ($T_a=25^\circ C$ Unless otherwise specified)

Item	Symbol	Conditions	Max.	Unit
Forward voltage drop **	V_{FM}	$I_{FM}=2.0A$	1.4	V
Reverse current **	I_{RRM}	$V_R=V_{RRM}$	500	µA
Reverse recovery time	t_{rr}	$I_f=0.1A, I_r=0.1A$	0.1	µs
Thermal resistance	$R_{th(j-c)}$	Junction to case	3.5	°C/W

- Mechanical characteristics

Mounting torque	Recommended torque	0.3 to 0.5	N·m
Approximate weight		2.3	g

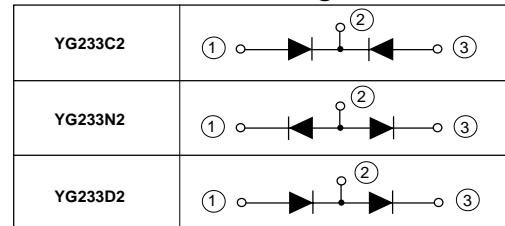
■ Outline drawings, mm



JEDEC

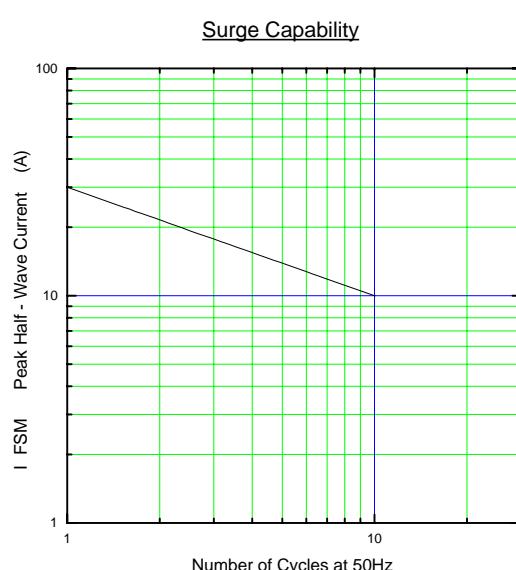
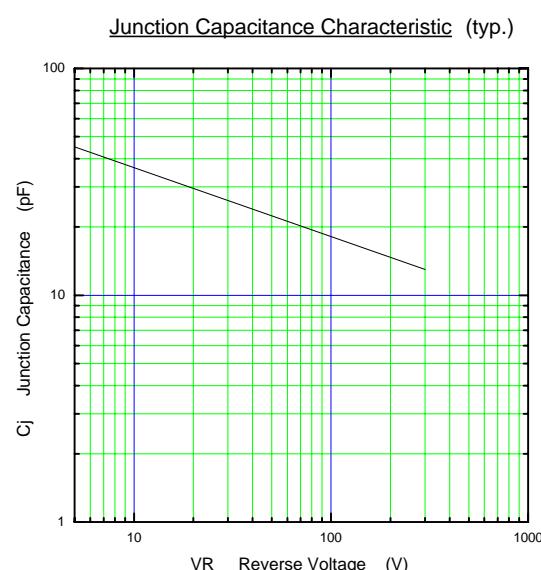
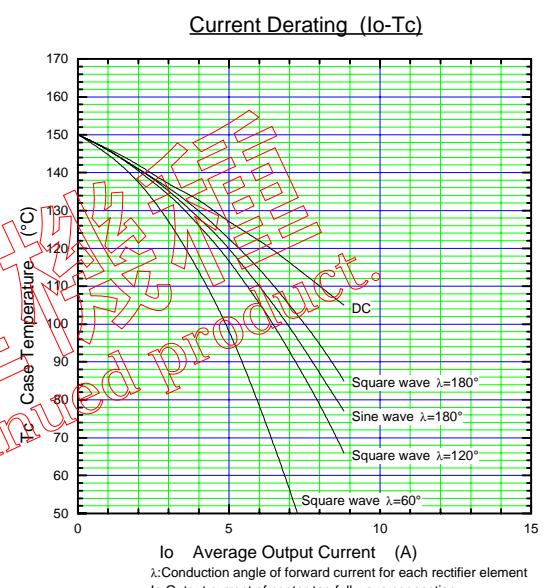
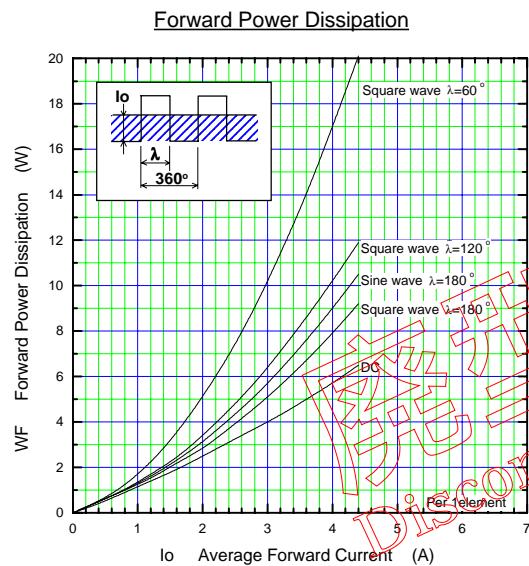
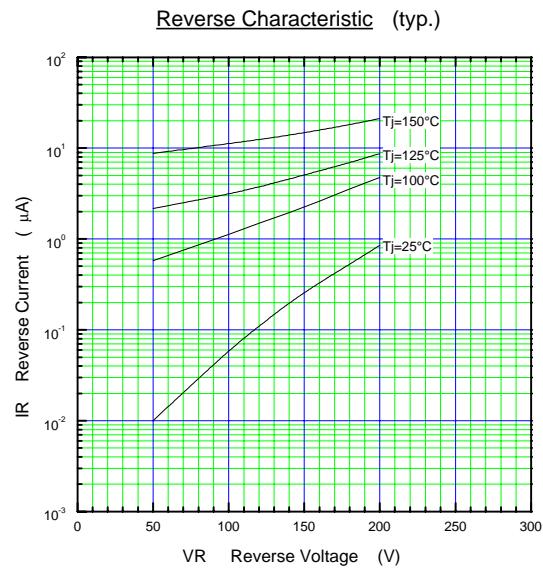
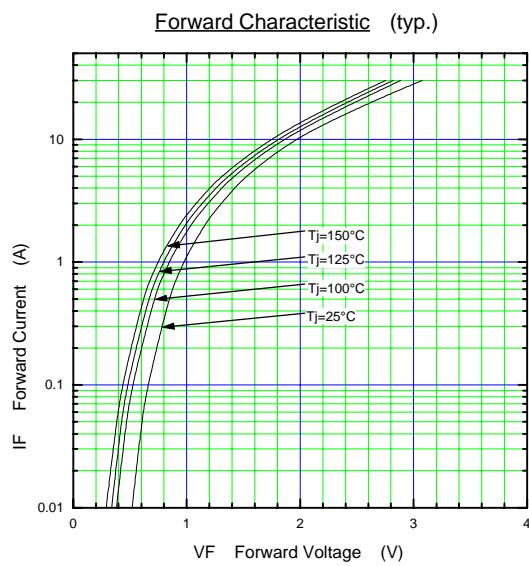
EIAJ SC-67

■ Connection diagram



Discontinued Product

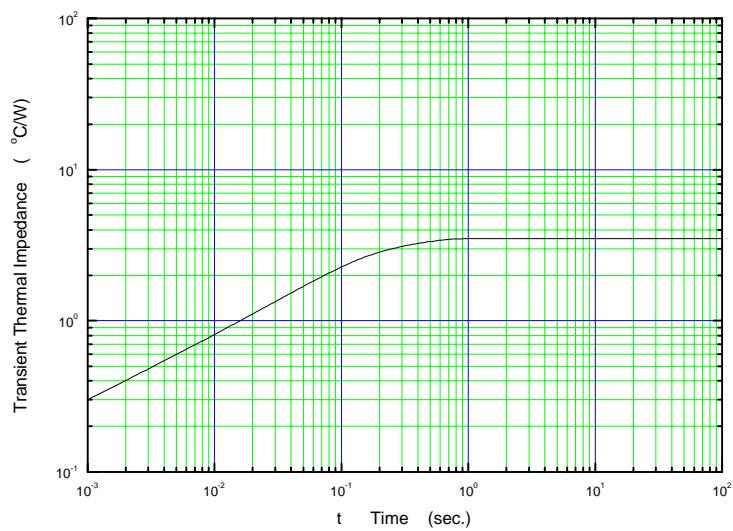
■ Characteristics



(200V / 8A)

YG233C2,N2,D2 (8A)

Transient Thermal Impedance



密型核子插
Discontinued product.